DATA SHEET

BST122
P-channel enhancement mode vertical D-MOS transistor

Product specification
File under Discrete Semiconductors, SC13b

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Philips Semiconductors

PHILIPS

P-channel enhancement mode vertical D-MOS transistor

BST122

DESCRIPTION

P-channel vertical D-MOS transistor in SOT89 envelope and intended for use in relay, high-speed and line-transformer drivers, using SMD-technology.

FEATURES

- Very low $R_{DS(on)}$
- Direct interface to C-MOS, TTL
- High-speed switching
- No second breakdown

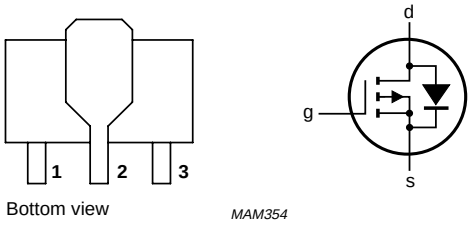
QUICK REFERENCE DATA

Drain-source voltage	$-V_{DS}$	max.	60	V
Gate-source voltage (open drain)	$\pm V_{GSO}$	max.	20	V
Drain current (DC)	$-I_D$	max.	0,25	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Drain-source ON-resistance				
$-I_D$ = 200 mA; $-V_{GS}$ = 10 V	$R_{DS(on)}$	max. typ.	10 7.5	Ω Ω
Transfer admittance				
$-I_D$ = 200 mA; $-V_{DS}$ = 15 V	$\lvert Y_{fs} \rvert$	typ.	125	mS

PINNING - SOT89

1 = source
2 = drain
3 = gate

PIN CONFIGURATION



Marking: LN

Fig.1 Simplified outline and symbol.

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RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	$-V_{DS}$	max.	60	V
Gate-source voltage (open drain)	$\pm V_{GSO}$	max.	20	V
Drain current (DC)	$-I_D$	max.	0.25	A
Drain current (peak)	$-I_{DM}$	max.	0.5	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Storage temperature range	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient (note 1)	$R_{th\ j\text{-}a}$	=	125	K/W

Note

1. Transistor mounted on a ceramic substrate: area = 2,5 cm^2; thickness = 0,7 mm.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Drain-source breakdown voltage				
$-I_D$ = 10 μA; V_{GS} = 0	$-V_{(BR)DSS}$	min.	60	V
Drain-source leakage current				
$-V_{DS}$ = 48 V; V_{GS} = 0	$-I_{DSS}$	max.	1	μA
Gate-source leakage current				
$-V_{GS}$ = 20 V; V_{DS} = 0	$-I_{GSS}$	max.	100	nA
Gate threshold voltage				
$-I_D$ = 1 mA; V_{DS} = V_{GS}	$-V_{GS(th)}$	min.	1.5	V
		max.	3.5	V
Drain-source ON-resistance				
$-I_D$ = 200 mA; $-V_{GS}$ = 10 V	$R_{DS(on)}$	max.	10	Ω
		typ.	7.5	Ω
Transfer admittance				
$-I_D$ = 200 mA; $-V_{DS}$ = 15 V	$\lvert Y_{fs} \rvert$	typ.	125	mS
Input capacitance at f = 1 MHz				
$-V_{DS}$ = 10 V; V_{GS} = 0	C_{iss}	typ.	30	pF
		max.	45	pF
Output capacitance at f = 1 MHz				
$-V_{DS}$ = 10 V; V_{GS} = 0	C_{oss}	typ.	20	pF
		max.	30	pF
Feedback capacitance at f = 1 MHz				
$-V_{DS}$ = 10 V; V_{GS} = 0	C_{rss}	typ.	5	pF
		max.	10	pF
Switching times (see Figs 2 and 3)				
$-I_D$ = 200 mA; $-V_{DD}$ = 50 V; $-V_{GS}$ = 0 to 10 V	t_{on}	typ.	4	ns
	t_{off}	typ.	10	ns

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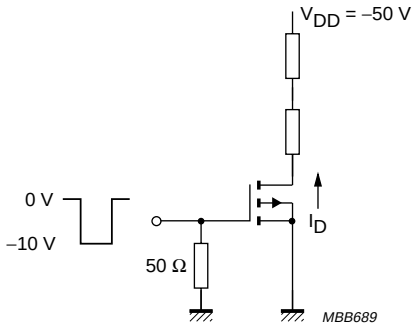


Fig.2 Switching times test circuit.

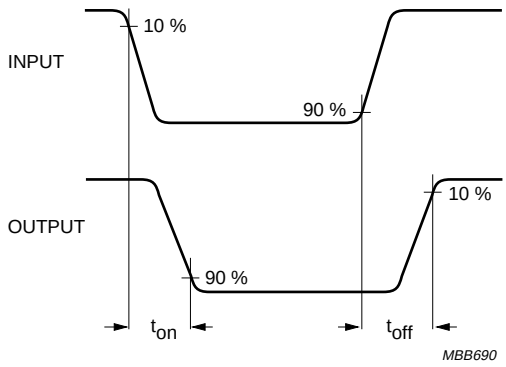


Fig.3 Input and output waveforms.

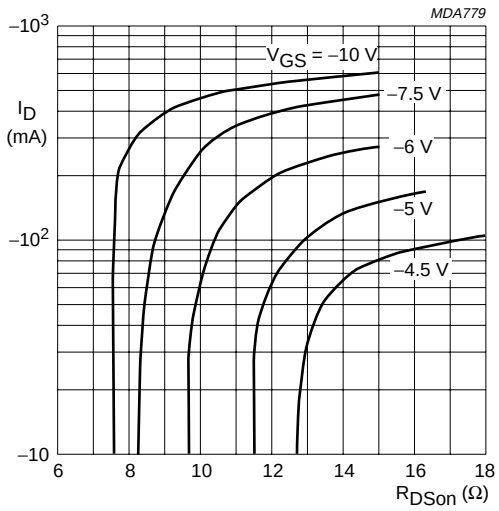


Fig.4 Drain current vs ON-resistance; T_j = 25 °C; typical values.

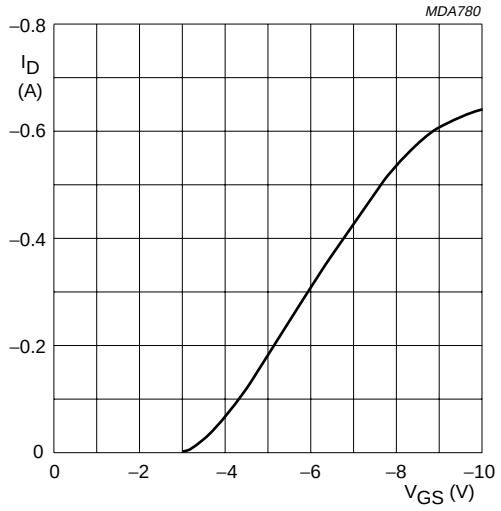


Fig.5 Transfer characteristics; T_j = 25 °C; $-V_{DS}$ = 10 V; typical values.

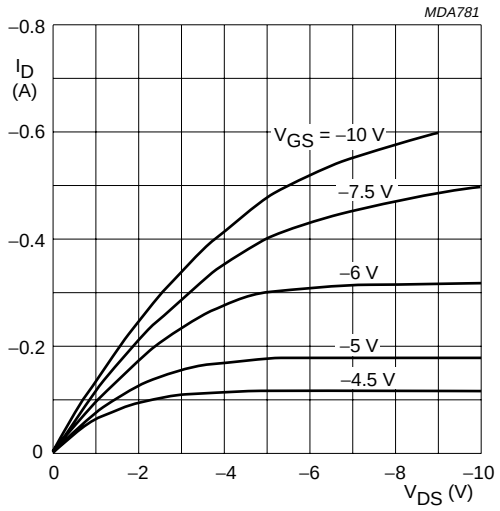
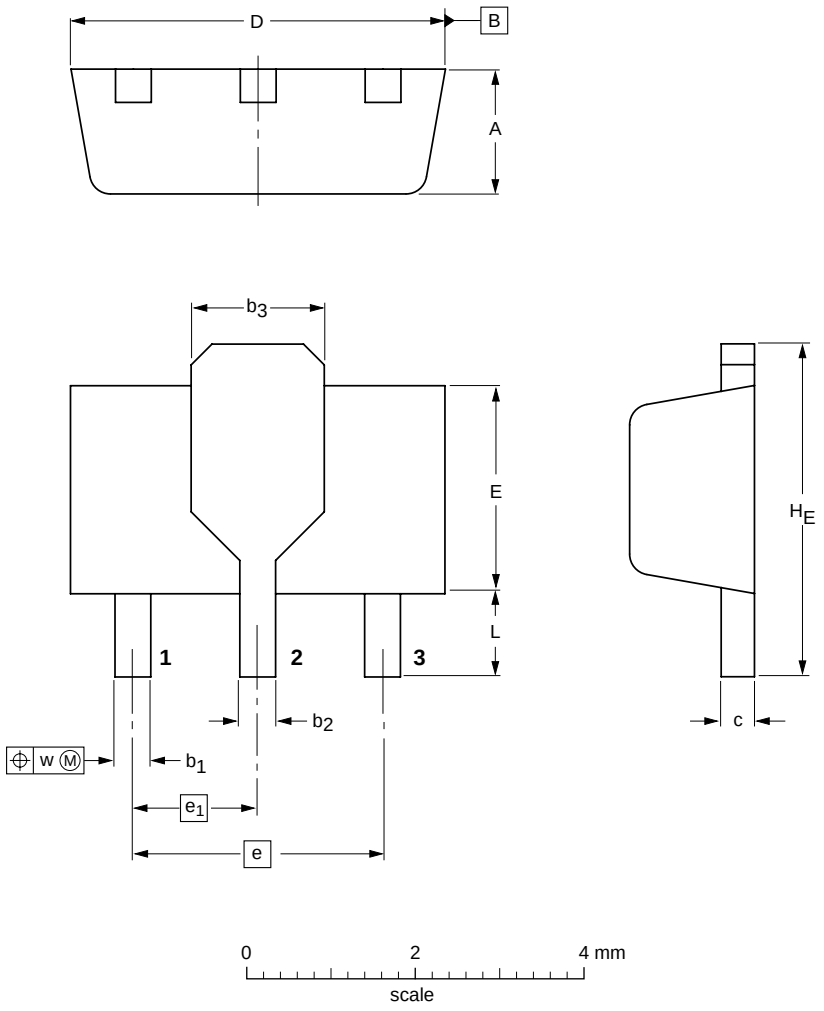


Fig.6 Output characteristics; T_j = 25 °C; typical values.

PACKAGE OUTLINES

Plastic surface mounted package; collector pad for good heat transfer; 3 leads **SOT89**



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_1	b_2	b_3	c	D	E	e	e_1	H_E	L min.	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.37	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	0.8	0.13

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT89						97-02-28

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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